

S/N 09/945,554

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes

Examiner: Thomas L Dickey

Serial No.: 09/945,554

Group Art Unit: 2826

Filed: August 30, 2001

Docket: 1303.028US1

Title: SRAM CELLS WITH REPRESSED FLOATING GATE MEMORY, LOW  
TUNNEL BARRIER INTERPOLY INSULATORS

**INFORMATION DISCLOSURE STATEMENT**

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,  
LEONARD FORBES

By his Representatives,  
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Date

29 Aug '04

By

Timothy B Clise  
Reg. No. 40,957

**CERTIFICATE UNDER 37 CFR 1.8:** The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 30<sup>th</sup> day of August, 2004.

Name

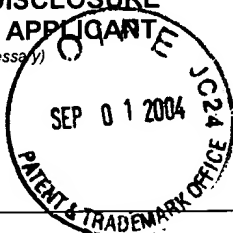
Amy Moriarty

Signature

[Signature]

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)

Complete if Known

Application Number	09/945,554
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2826
Examiner Name	Dickey, Thomas

Sheet 1 of 1

Attorney Docket No: 1303.028US1

**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
	US-4,688,078	08/18/1987	Hseih, Ning	257	321	12/11/1985
	US-4,939,559	07/03/1990	DiMaria, D. J., et al.	257	38	04/01/1986
	US-5,488,612	01/30/1996	Heybruck, W. F.	714	725	10/04/1993
	US-5,959,465	09/28/1999	Beat, R.	326	39	12/29/1995
	US-6,377,070	04/23/2002	Forbes, Leonard	326	41	02/09/2001
	US-6,514,842	02/04/2003	Prall, K. D., et al.	438	593	08/08/2001
	US-6,730,575	05/04/2004	Eldridge, Jerome M.	257	310	08/30/2001

**FOREIGN PATENT DOCUMENTS**

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		AFANAS'EV, V. , et al., "Electron energy barriers between (100)Si and ultrathin stacks of SiO <sub>2</sub> , Al <sub>2</sub> O <sub>3</sub> , and ZrO <sub>2</sub> insulators", <u>Applied Physics Letters</u> , 78(20), (May 14, 2001),3073-3075	
		ELDRIDGE, J.M. , et al., "The Growth of Thin PbO Layers on Lead Films", <u>Surface Science Vol. 40</u> , (1973),512-530	
		GRIMBLOT, JEAN , et al., "I. Interaction of Al films with O <sub>2</sub> at low pressures", <u>Journal of the Electrochemical Society</u> , 129(10), (1982),2366-2368	
		GRIMBLOT, J. , et al., "II. Oxidation of Aluminum Films", <u>J. Electrochem.</u> , 129, (1982),2369-2372	
		LUAN, H. F., "High Quality Ta <sub>2</sub> O <sub>5</sub> Gate Dielectrics with Tox,eq<10A", <u>IEDM Technical Digest. International Electron Devices Meeting</u> , (December 5-8, 1999),141-143	
		ROBERTSON, J. , "Schottky barrier heights of tantalum oxide, barium strontium-titanate, lead titanate, and strontium bismuth tantalate", <u>Applied Physics Letters</u> , 74(8), (February 22, 1999),1168-1170	
		SHI, YING , et al., "Tunneling Leakage Current in Ultrathin (<4 nm) Nitride/Oxide Stack Dielectrics", <u>IEEE Electron Device Letters</u> , 19(10), (October 1998),388-390	
		YAN, J. , "Structural and electrical characterization of TiO <sub>2</sub> grown from titanium tetrakis-isopropoxide (TTIP) and TTIP/H <sub>2</sub> O ambients", <u>Journal of Vacuum Science Technology B</u> 14(3), (1996),pp. 1706-1711	

**EXAMINER****DATE CONSIDERED**

Substitute Disclosure Statement Form (PTO-1448)

\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached